



DONGGUAN NANJING ELECTRONICS LTD.,

NPN General Purpose Transistor

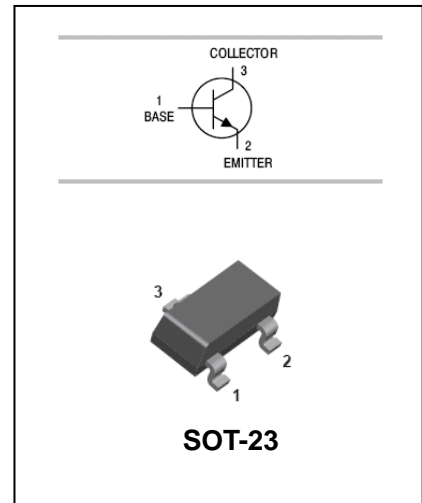
MMBTA13/MMBTA14

FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMBTA63/MMBTA64).
- High current gain.

APPLICATIONS

- Ideal for medium power amplification and switching



ORDERING INFORMATION

Type No.	Marking	Package Code
MMBTA13	K2D	SOT-23
MMBTA14	K3D	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT	
V _{CBO}	collector-base voltage	MMBTA13	30	V
		MMBTA14	30	
V _{CEO}	collector-emitter voltage	MMBTA13	30	V
		MMBTA14	30	
V _{EBO}	emitter-base voltage	10	V	
I _C	collector current (DC)	0.3	A	
P _C	Collector dissipation	0.35	W	
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W	
T _j , T _{stg}	junction and storage temperature	-55-150	°C	

NPN General Purpose Transistor

MMBTA13/MMBTA14

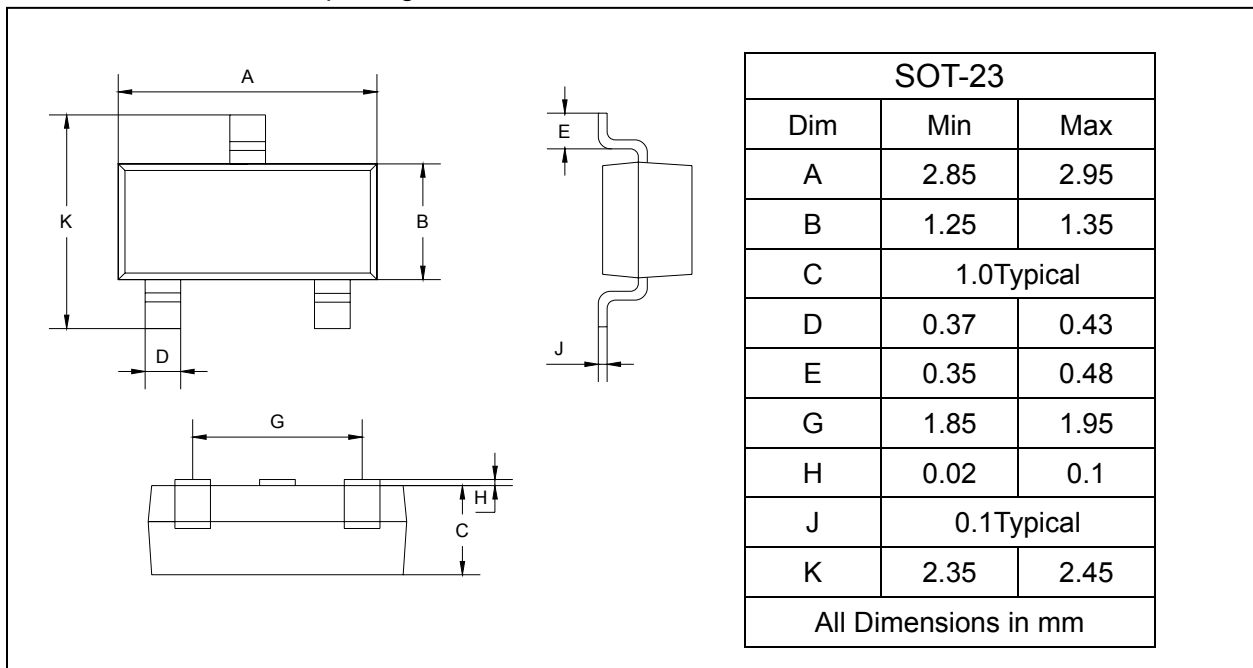
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage MMBTA13 MMBTA14	$I_C=100\mu A, I_E=0$	30 30	-	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage MMBTA13 MMBTA14	$I_C=0.1mA, I_B=0$	30 30	-	V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A, I_C=0$	10	-	V
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30V$	-	0.1	μA
I_{CEO}	collector cut-off current	$I_E = 0; V_{CE} = 10V$	-	0.1	μA
h_{FE}	DC current gain	MMBTA13 $V_{CE} = 5V; I_C = 10mA$	5000	-	
		MMBTA14 $V_{CE} = 5V; I_C = 10mA$	10000		
		MMBTA13 $V_{CE} = 5V; I_C = 100mA$	10000		
		MMBTA14 $V_{CE} = 5V; I_C = 100mA$	20000		
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = 100mA; I_B = 0.1mA$	-	1.5	V
f_T	transition frequency	$I_C = 10mA; V_{CE} = 5.0V;$ $f = 100MHz$	125	-	MHz

PACKAGE OUTLINE

Plastic surface mounted package

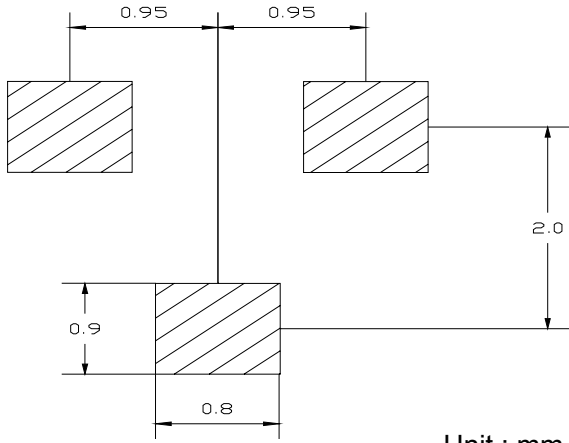
SOT-23



NPN General Purpose Transistor

MMBTA13/MMBTA14

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
MMBTA13/MMBTA14	SOT-23	3000/Tape&Reel